

# Automotive Low Power 3D Magnetic Sensor with I<sup>2</sup>C Interface

## TLE493D-A1B6

3D Hall Sensor

Data Sheet

Rev. 1.2, 2019-04-09

Sense & Control

## Table of Contents

<b>1</b>	<b>Product Description</b> .....	<b>5</b>
1.1	Target Applications .....	5
1.2	Features .....	5
<b>2</b>	<b>Functional Description</b> .....	<b>7</b>
2.1	General .....	7
2.1.1	Power mode control .....	7
2.1.2	Sensing part .....	8
2.2	Pin Configuration (top view) .....	8
2.3	Definition of Magnetic Field .....	9
2.4	Sensitive Area .....	9
2.5	Application circuit .....	10
<b>3</b>	<b>Specification</b> .....	<b>11</b>
3.1	Absolute Maximum Ratings .....	11
3.2	Operating Range .....	11
3.3	Electrical Characteristics .....	13
3.4	Magnetic Characteristics .....	14
3.5	Temperature measurement (default = activated) .....	16
3.6	Overview of Modes .....	16
<b>4</b>	<b>Interface and Timing Description</b> .....	<b>17</b>
<b>5</b>	<b>Package Information</b> .....	<b>19</b>
5.1	Package Parameters .....	19
5.2	Package Outlines .....	19
<b>6</b>	<b>Revision History</b> .....	<b>22</b>

## List of Tables

Table 1	Ordering Information .....	6
Table 2	TSOP6 pin description and configuration (see <a href="#">Figure 3</a> ) .....	8
Table 3	Absolute maximum ratings.....	11
Table 4	Electrostatic Discharge Protection .....	11
Table 5	Operating Range .....	11
Table 6	Electrical setup .....	13
Table 7	Initial Magnetic Characteristics .....	14
Table 8	Sensor Drifts.....	14
Table 9	Conversion table for 12Bit.....	15
Table 10	Conversion table for 8Bit.....	15
Table 11	Temperature Measurement Characteristics .....	16
Table 12	Overview of modes and its corresponding current consumption with sample rates .....	16
Table 13	Interface and timing.....	17
Table 14	Package Parameters .....	19

## List of Figures

Figure 1	Image of TLE493D-A1B6 in TSOP6 package .....	5
Figure 2	Block Diagram .....	7
Figure 3	Pinout .....	8
Figure 4	Definition of Magnetic Field Direction .....	9
Figure 5	Center of Sensitive Area (all dimensions in mm) .....	9
Figure 6	Application circuit with external power supply and $\mu\text{C}$ .....	10
Figure 7	I <sup>2</sup> C readout frame, ADC conversion and related timing .....	18
Figure 8	I <sup>2</sup> C timing specification .....	18
Figure 9	Image of TLE493D-A1B6 in TSOP6.....	19
Figure 10	Footprint for PG-TSOP6-6-5 and PG-TSOP6-6-8 (all dimensions in mm) .....	19
Figure 11	Package Outlines (all dimensions in mm) .....	20
Figure 12	Packing (all dimensions in mm).....	21

## Product Description

### 1 Product Description

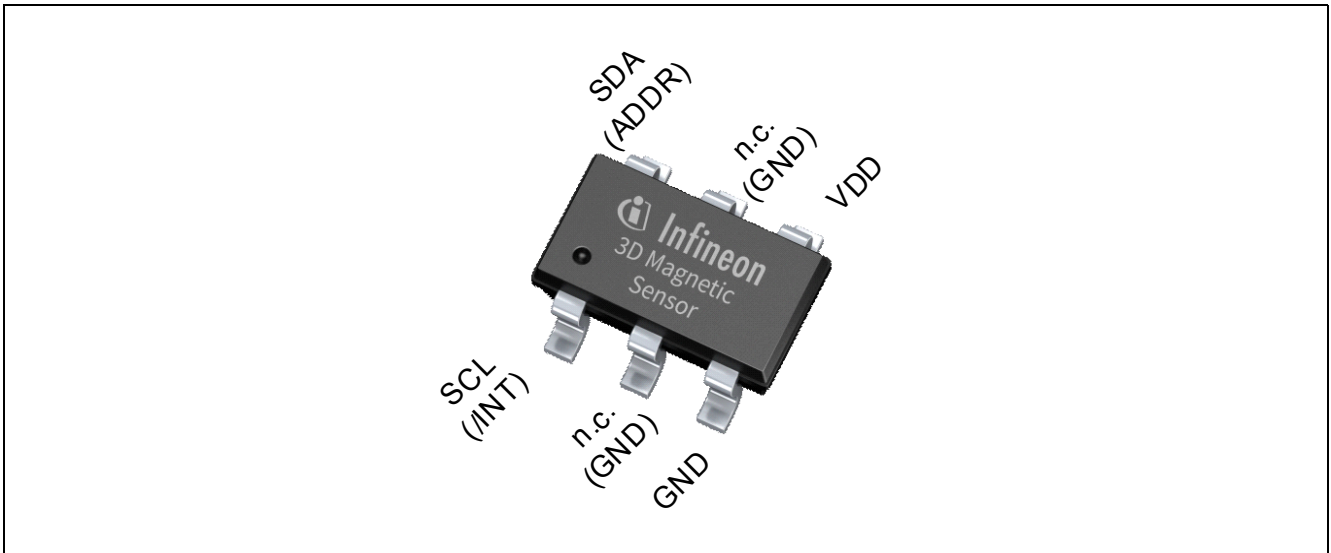
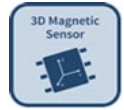


Figure 1 Image of TLE493D-A1B6 in TSOP6 package

#### 1.1 Target Applications

The TLE493D-A1B6 is designed for linear, rotary and 3D position sensing in automotive applications, such as:

- Gear stick
- Turnlight and wiper control elements
- Multi function knobs
- Pedal/valve position sensing
- Integration in the top column module for direction indicator for instance

#### 1.2 Features

- 3D magnetic flux density sensing
- Ultra low power consumption with typical 5 $\mu$ A during operation (typical 6Hz)
- Power-down mode with typical 7nA power consumption
- Digital output via 2-wire standard I<sup>2</sup>C interface
- 12 bit data resolution for each measurement direction incl. chip temperature
- B<sub>x</sub>, B<sub>y</sub> and B<sub>z</sub> linear field measurement of  $\pm 60$ mT
- Excellent matching of X/Y measurement for accurate angle sensing
- Variable update frequencies and power modes (configurable during operation)
- Supply voltage range = 2.9V...3.5V
- Temperature range T<sub>j</sub> = -40°C...125°C
- Triggering by external  $\mu$ C possible via I<sup>2</sup>C protocol
- Interrupt signal to signalise end of measurement cycle
- Temperature measurement

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Product Description

- Automotive qualified
- Small 6-pin TSOP package

**Table 1**    **Ordering Information**

Product Name	Marking	Ordering Code	Package
TLE493D-A1B6	EA	SP001368598	PG-TSOP6-6-5

Functional Description

## 2 Functional Description

### 2.1 General

Description of the Block diagram and its functions.

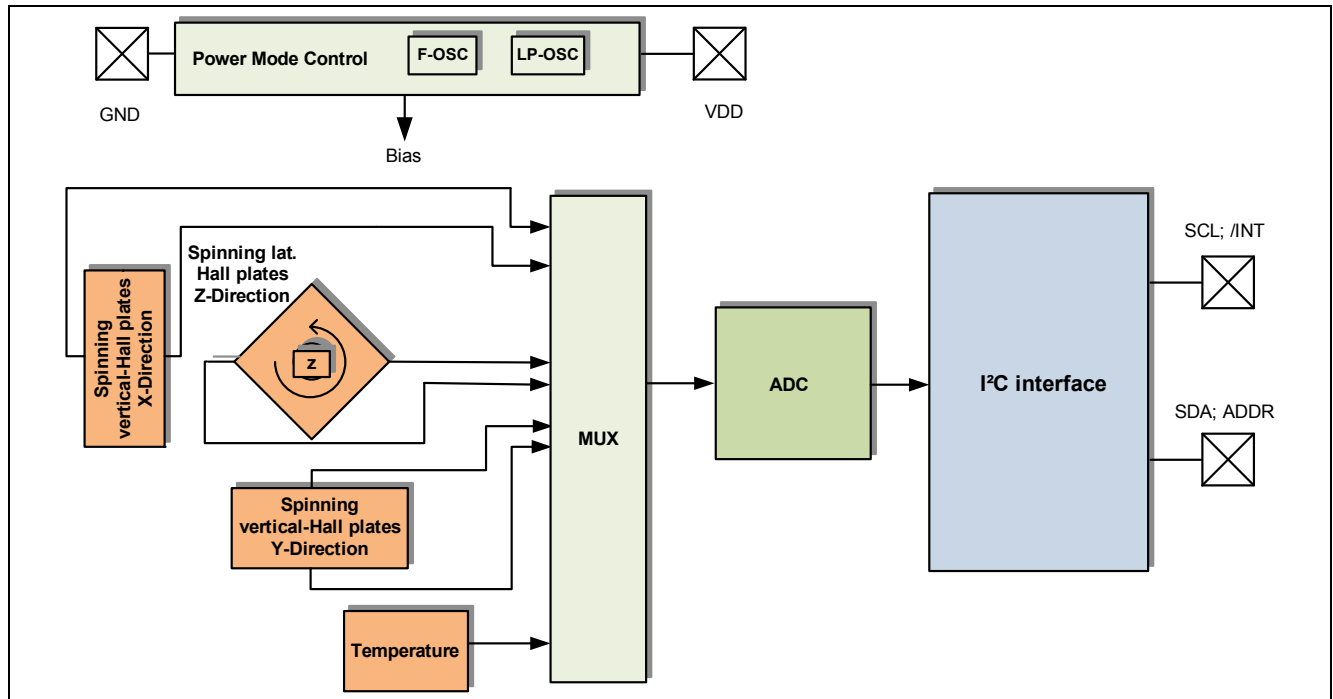


Figure 2 Block Diagram

The IC consists of three main function units containing following building blocks:

- The power mode control system, containing a low-power oscillator, basic biasing, accurate reset, undervoltage detection and a fast oscillator.
- The sensing part, containing the HALL biasing, HALL probes with multiplexers and ADC. Furthermore a temperature sensor is implemented.
- The I<sup>2</sup>C interface, containing the register files and I/O pads.

#### 2.1.1 Power mode control

The power mode control provides the power distribution in the IC, a power-on reset function and a specialized low-power oscillator as clock source. Additionally it is handling the start-up behavior.

- On start-up this unit:
  - activates the biasing, provides an accurate reset detector and fast oscillator
  - interprets the applied voltage level on ADDR pin as logical “0” or “1”. This represents than the address sensor enters low power mode (and can be configured via I<sup>2</sup>C interface)
- After re-configuration a measurement cycle is performed regularly containing of:
  - activation the internal biasing, checks for reset condition and provides the fast oscillator
  - the HALL biasing

### Functional Description

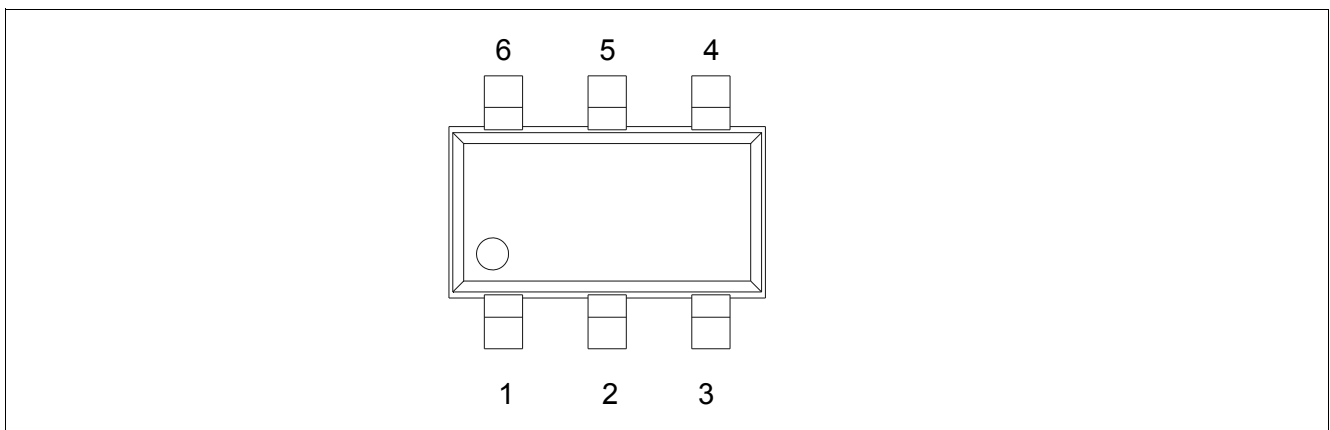
- the measurement of the three HALL probe channels sequentially incl. temperature (default = activated)
  - and enters the configured mode again
- In any case functions are only executed if the supply voltage is high enough, otherwise the reset circuit will halt the state machine until the level is reached and restarts its operation afterwards. The functions are also restarted if a reset event occurs in between (parameter "Reset Level" in [Chapter 3.2](#)).

### 2.1.2 Sensing part

Performs the measurements of the magnetic field in X, Y and Z direction. Each X, Y and Z-Hall probe is connected sequentially to a multiplexer, which is then connected to an Analog to Digital Converter (ADC). Optional, the temperature (default = activated) is determined as well after the three Hall channels.

### 2.2 Pin Configuration (top view)

**Figure 3** shows the pinout of the TLE493D-A1B6.



**Figure 3** Pinout

**Table 2** TSOP6 pin description and configuration (see [Figure 3](#))

Pin No.	Name	Description
1	SCL /INT	Interface serial clock pin (input) Interrupt pin, signals a finished measurement cycle, open drain
2	GND	connect to GND
3	GND	Ground Pin
4	V <sub>DD</sub>	Supply Pin
5	GND	connect to GND
6	SDA ADDR	Interface serial data pin (input/output), open drain Sensor ID configuration during power up



Functional Description

2.3 Definition of Magnetic Field

A positive field is considered as South-Pole facing the corresponding Hall element.

Figure 4 shows the definition of the magnetic field directions X, Y, Z of the TLE493D-A1B6.

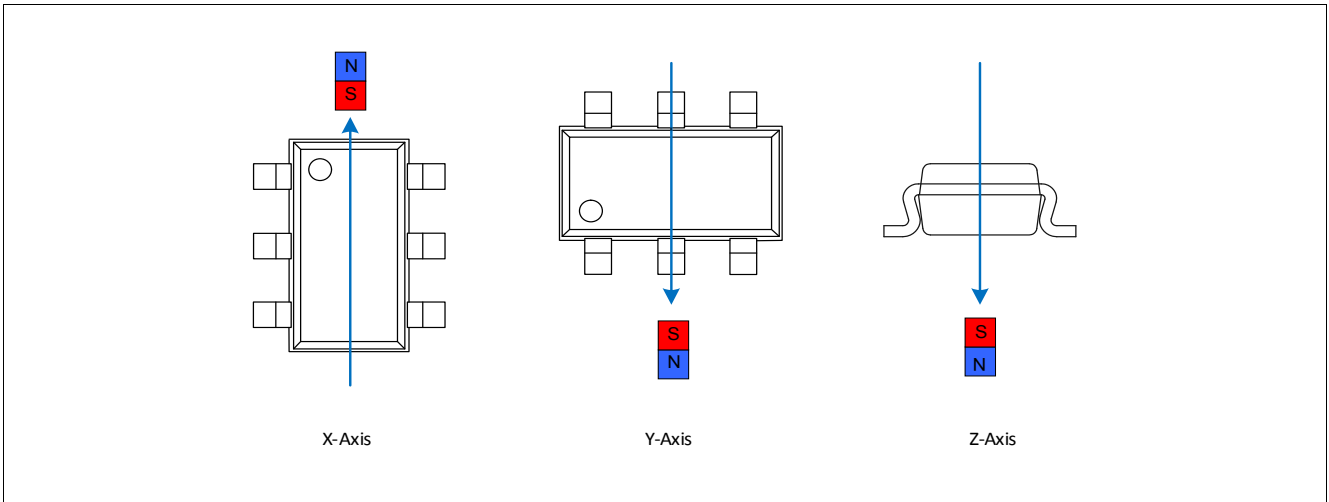


Figure 4 Definition of Magnetic Field Direction

2.4 Sensitive Area

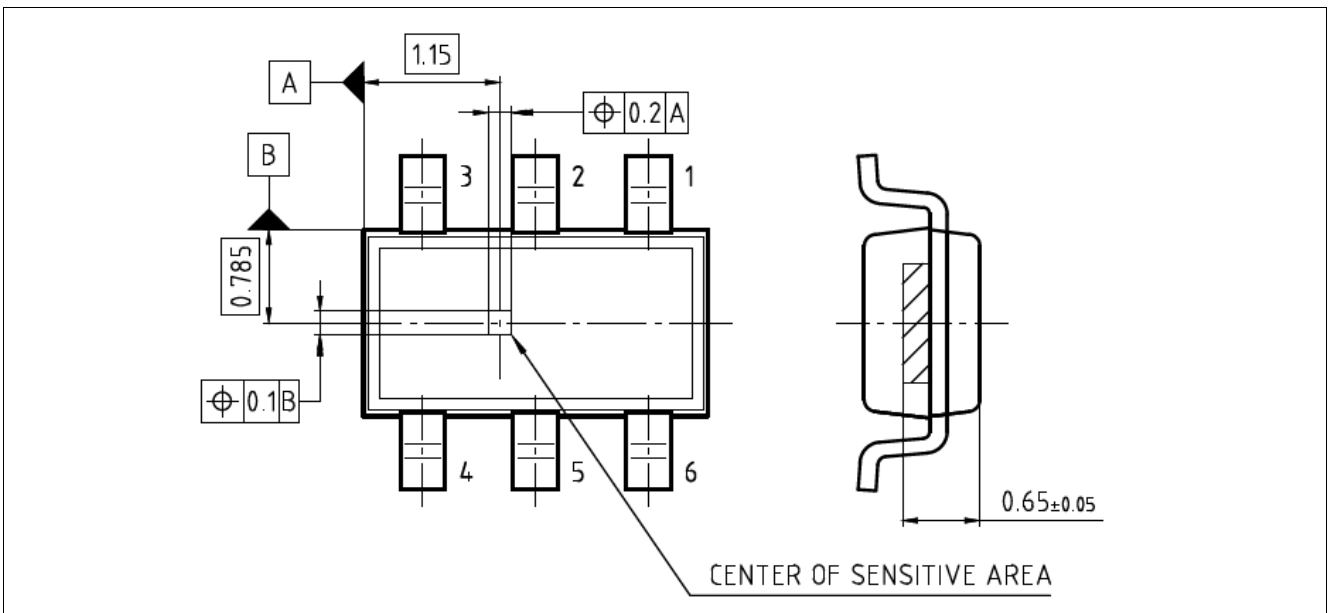


Figure 5 Center of Sensitive Area (all dimensions in mm)

Functional Description

2.5 Application circuit

The use of an interrupt line is optional, but highly recommended to ensure proper and efficient readout of the sensor data.

The pull-up resistor values of the I<sup>2</sup>C bus have to be calculated in a way to fulfill the rise- and fall time specification of the interface for the given worst case parasitic (capacitive) load of the actual application setup.

Please note: too small resistive values  $R_{1/2}$  have to be prevented to avoid unnecessary power consumption during interface transmissions, especially for low-power applications.

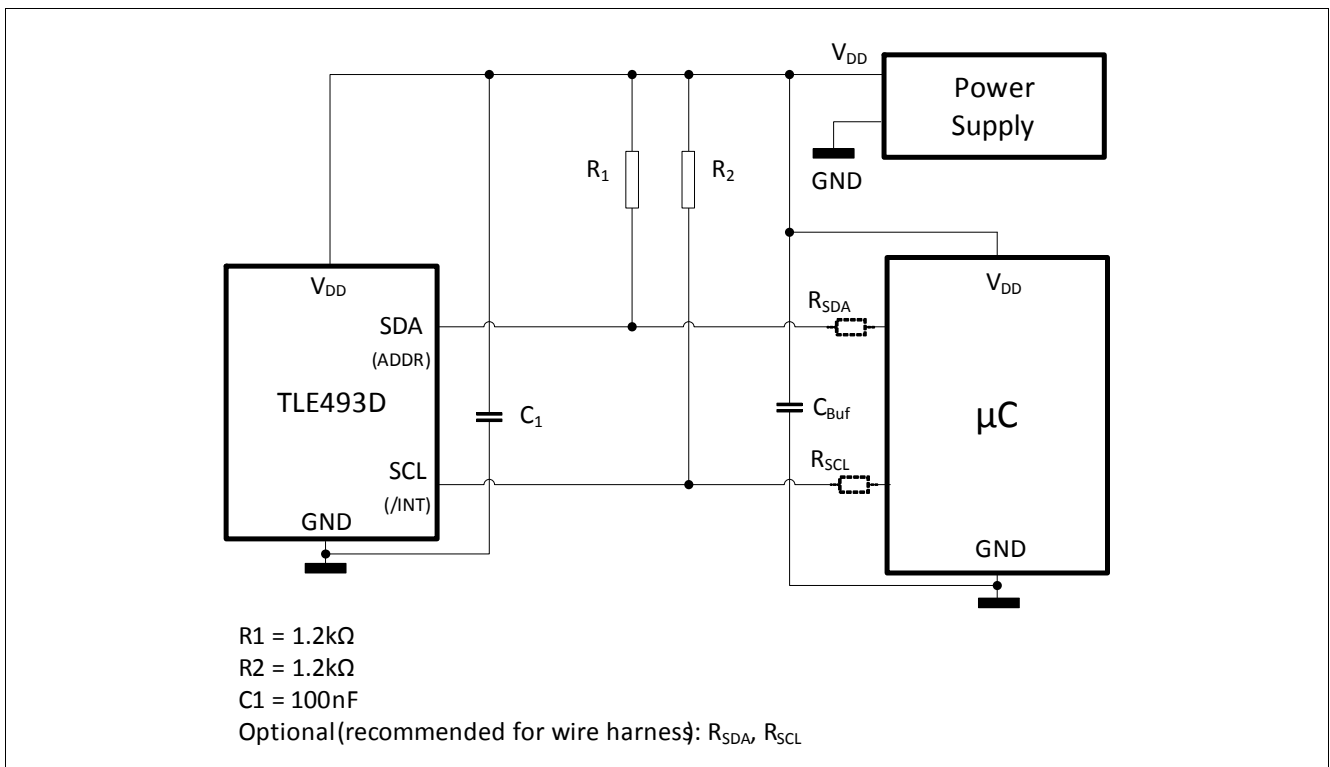


Figure 6 Application circuit with external power supply and µC

For additional EMC precaution in harsh environments,  $C_1$  may be implemented by two 100nF capacitors in parallel, which should be already given by  $C_{Buf}$  near the µC and/or power supply.

Specification

### 3 Specification

#### 3.1 Absolute Maximum Ratings

**Attention:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Furthermore, only single error cases are assumed. More than one stress/error case may also damage the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During absolute maximum rating overload conditions the voltage on VDD pins with respect to ground (VSS) must not exceed the values defined by the absolute maximum ratings.

**Table 3 Absolute maximum ratings**

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Junction temperature	$T_j$	-40	–	125	°C	–
Voltage on V <sub>DD</sub>	V <sub>DD</sub>	-0.3	–	3.5	V	–
Magnetic field	B <sub>max</sub>	–	–	±1	T	–
Voltage range on any pin to GND	V <sub>max</sub>	-0.1	–	3.5	V	open-drain outputs are not current limited.

**Table 4 Electrostatic Discharge Protection**

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
ESD voltage	V <sub>HBM</sub>			±2.0	kV	<sup>1)</sup> R = 1.5 kΩ, C = 100 pF
	V <sub>CDM</sub>			±0.5	kV	<sup>2)</sup>
					±0.75	kV

1) Human Body Model (HBM) tests according to ANSI/ESDA/JEDEC JS-001.

2) Charged Device Model (CDM), ESD susceptibility according to JESD22-C101.

#### 3.2 Operating Range

**Table 5 Operating Range**

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Operating temperature	$T_j$	-40	–	125	°C	$T_j = T_a + 3^\circ\text{C}$ in fast mode
Supply voltage	V <sub>DD</sub>	2.9	3.3	3.5	V	Supply voltage must be above reset level
Reset level	V <sub>Res</sub>	2.2	2.5	2.9	V	min. ADC operating level

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Specification

*Note: To provide this ultra low power consumption figures, the chip does not use a classic (and current consuming) reset concept. The implemented reset focus on ensuring a proper supply for the ADC operation only (so it inhibits the ADC reliably until the sensor supply is high enough). Thus, the sensor relays on a proper supply ramp incl. 3.3mA current consumption during power-on to ensure it is initialized correctly, typically a monotonic rise of Vdd from zero to 3.3V within less than 10 $\mu$ s and without over/undershoots larger than 300mV. The I<sup>2</sup>C reset feature of the sensor shall be used by the  $\mu$ C after power-up. If an supply monitoring is used in the system (e.g. brown-out detector etc.), it is also recommended to use the I<sup>2</sup>C reset of the sensor upon events detected by this monitor. In any case, an external supply switch (either provided by a System-Basis-Chip solution which includes a supply-enable feature, a Bias-Resistor-Transistor device, a capable  $\mu$ C GPIO pin, etc.) shall allow a power-cycle of the sensor as backup for high availability applications to cope with any form of Vdd ramps (including potential EMC influences).*

Specification

### 3.3 Electrical Characteristics

Note: All specification parameters refer to 3.3V  $\pm 5\%$  nominal supply  $V_{DD}$  on the pins directly. Typical values refer to 25°C and to 3.3V  $\pm 5\%$  nominal supply.

**Table 6 Electrical setup**

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Supply current <sup>1)</sup>	$I_{DD}$	–	7	–	nA	power-down mode, all off
		–	5	–	$\mu$ A	ultra low power mode
		–	57	–	$\mu$ A	low power mode (default after power on)
		–	3.3	–	mA	fast mode
Average operating current	$I_{DD\_op}$	–	3.3	–	mA	during active ADC measurement for about 172 $\mu$ s <sup>2)3)</sup>
Input voltage low threshold <sup>4)</sup>	$V_{IL}$	–	–	30	% $V_{DD}$	all input pads
Input voltage high threshold <sup>4)</sup>	$V_{IH}$	70	–	–	% $V_{DD}$	all input pads
Input voltage hysteresis <sup>4)</sup>	$V_{I\_Hyst}$	5	–	–	% $V_{DD}$	all input pads
Output voltage low level @ 3mA load	$V_{OL}$	–	–	0.4	V	all output pads, static load
Output high level	$V_{OH}$	–	$V_{DD}$	–	V	given by ext. pull-up resistor

- 1) Average values considering measuring period and power-down
- 2) Typical conversion time is 172 $\mu$ s with temperature and 129 $\mu$ s without
- 3) Current at Pull ups needs to be considered for power supply dimensioning, consider minimum 10mA for the power supply for the sensor only
- 4) Based on I<sup>2</sup>C standard 1995 for  $V_{DD}$  related input levels

Note: The average supply current  $I_{DD}$  in the 2 low power modes and I<sup>2</sup>C triggered mode will decrease by about 25% when the temperature measurement is disabled.

Specification

3.4 Magnetic Characteristics

**Table 7 Initial Magnetic Characteristics<sup>1)</sup>**

Values for 25°C, 0h and  $V_{DD} = 3.3V$ , unless otherwise stated

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Magnetic linear range <sup>2)</sup>	$B_{xyz\_LIN}$	$\pm 60$	–	–	mT	Bx, By and Bz for $-40^{\circ}C < T_{junction} < +125^{\circ}C$
Offset	$B_{OZ}$	-1.8	$\pm 0.2$	+1.8	mT	Offset of Bz
	$B_{OXY}$	-0.75	$\pm 0.2$	+0.75	mT	Offset of Bx and By
Sensitivity	$Sens$	5.5	7.7	10.5	LSB <sub>12</sub> / mT	Bx, By and Bz; (12bit)
X to Y magnetic matching <sup>3)</sup>	$M_{X/Y}$	-15	–	+15	%	
X/Y to Z magnetic matching <sup>3)</sup>	$M_{X/YZ}$	-25	–	+25	%	
Resolution 12-bit readout <sup>4)</sup>	$Res_{12}$	95	130	182	$\mu T$ / LSB <sub>12</sub>	
Resolution 8-bit readout <sup>4)</sup>	$Res_8$	1.52	2.08	2.91	mT/ LSB <sub>8</sub>	
Magnetic initial noise (rms)	$B_{iNeff}$	–	0.1	0.5	mT	rms = 1 sigma
Magnetic hysteresis	$B_{HYS}$	–	1	–	LSB <sub>12</sub>	due to quantization effects

- 1) Magnetic test on wafer level. It is assumed that initial variations are stored and compensated in the external  $\mu C$  during module test and calibration.
- 2) Not subject to production test - verified by design/characterization; magnetic minimum linear range is valid for the specified 0h sensitivity range
- 3) The matching is defined for sensitivity values of Bx (=X), By (=Y) and Bz (=Z) as:  
X/Y matching:  $100 \cdot 2 \cdot (X-Y)/(X+Y)$  [in %], X/Y to Z matching:  $100 \cdot 2 \cdot (X+Y-2 \cdot Z)/(X+Y+2 \cdot Z)$  [in %]
- 4) Resolution is calculated as  $1/Sensitivity$  (and multiplied by 16 for 8-bit value).

**Table 8 Sensor Drifts<sup>1)</sup>**

Values for  $V_{DD} = 3.3V \pm 5\%$ ,  $T_j = -40$  to  $125^{\circ}C$ , static magnetic field within usable linear range

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Sensitivity drift	$Sens_D$	-15	$\pm 5$	+15	%	Bx, By and Bz
Offset drift	$B_{O\_DZ}$	-1.6	$\pm 0.2$	+1.6	mT	Bz @ 0mT
	$B_{O\_DXY}$	-0.75	$\pm 0.2$	+0.75	mT	Bx and By @ 0mT
X to Y magnetic matching drift <sup>2)</sup>	$M_{XY\_D}$	-9	$\pm 1$	+9	%	
X/Y to Z magnetic matching drift <sup>2)</sup>	$M_{X/YZ\_D}$	-15	$\pm 10$	+15	%	
Temperature compensation <sup>3)</sup>	$TC_0$	–	$\pm 0$	–	ppm/K	Bx, By and Bz (default)
	$TC_1$	–	-750	–		Bx, By and Bz (option 1)
	$TC_2$	–	-1500	–		Bx, By and Bz (option 2)
	$TC_3$	–	+350	–		Bx, By and Bz (option 3)

Specification

**Table 8 Sensor Drifts<sup>1)</sup>**

Values for  $V_{DD} = 3.3V \pm 5\%$ ,  $T_j = -40$  to  $125\text{ }^\circ\text{C}$ , static magnetic field within usable linear range

Parameter	Symbol	min	typ	max	Unit	Note/Condition
DNL (Differential Non Linearity)	DNL	–	$\pm 2^4$	–	LSB <sub>12</sub>	Bx, By and Bz
INL (Integral Non Linearity)	INL	–	$\pm 2^4$	–	LSB <sub>12</sub>	Bx, By and Bz
Magnetic noise (rms)	$B_{Neff}$	–	–	1	mT	rms = 1 sigma

- 1) Not subject to production test, verified by design/characterization. Drifts are changes from the initial characteristics due to external influences.
- 2) The matching is defined for sensitivity values of Bx (=X), By (=Y) and Bz (=Z) as:  
X/Y matching:  $100 \cdot 2 \cdot (X-Y)/(X+Y)$  [in %], X/Y to Z matching:  $100 \cdot 2 \cdot (X+Y-2 \cdot Z)/(X+Y+2 \cdot Z)$  [in %]
- 3) The temperature sensitivity variation alone is +13%. It is mandatory to set the TC value before performing data readouts of the sensor on given magnetic points or angles for sensitivity trimming (with external microcontroller as zero-hour trim in production).
- 4) Represents 0.1%FSR.

**Conversion register value to magnetic field value:**

**Table 9 Conversion table for 12Bit**

	MSB	Bit11	Bit10	Bit9	Bit8	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	LSB
	-2048	1024	512	256	128	64	32	16	8	4	2	1
e.g.	1	1	1	1	0	0	0	0	1	1	1	1

The conversion is realized by the two's complement. Please use following table for transformation:

Example for 12Bit read out: 1111 0000 1111:  $-2048 + 1024 + 512 + 256 + 0 + 0 + 0 + 0 + 8 + 4 + 2 + 1 = -241$  LSB

Calculation to mT:  $-241 \text{ LSB} \cdot 0.130 \text{ mT/LSB} = -31.3 \text{ mT}$

**Table 10 Conversion table for 8Bit**

	MSB	Bit11	Bit10	Bit9	Bit8	Bit7	Bit6	LSB
	-128	64	32	16	8	4	2	1
e.g.	0	1	0	1	1	1	0	1

Example for 8-Bit read out: 0101 1101:  $0 + 64 + 0 + 16 + 8 + 4 + 0 + 1 = 93$  LSB

Calculation to mT:  $93 \text{ LSB} \cdot 2.08 \text{ mT/LSB} = 193.4 \text{ mT}$

Specification

### 3.5 Temperature measurement (default = activated)

**Table 11** Temperature Measurement Characteristics<sup>1)</sup>

Parameter	Symbol	min	typ	max	Unit	Note/Condition
Digital value @ 25°C <sup>2)</sup>	$T_{25}$	974	1217	1460	LSB <sub>12</sub>	-
Resolution 12bit	$T_{Res12}$	0.24	0.28	0.32	°C/LSB <sub>12</sub>	-
Resolution 8bit	$T_{Res8}$	-	4.48	-	°C/LSB <sub>8</sub>	-
Accuracy	$T_{ACC}$	-	±7	-	°C	-

- 1) The temperature measurement is not trimmed on the sensor. An external  $\mu C$  can measure the sensor during module production and implement external trimming to gain higher accuracies.
- 2) Theoretical possible measurement range from -50°C to 150°C

### 3.6 Overview of Modes

**Table 12** Overview of modes and its corresponding current consumption with sample rates<sup>1)</sup>

Mode	Register Address	Typ. Update Rate	Typ. IDD	Remark
Power Down	-	-	7 nA	-
Low Power	Reg 11, Bit 0..1 = 00 Reg 13, Bit 7..5= 001	94 Hz	57 $\mu A$	Default after Power On
	Reg 11, Bit 0..1 = 00 Reg 13, Bit 7..5= 100	6 Hz	5 $\mu A$	Ultra low power mode
Fast Mode	Reg 11: Bit 0..1 = 11 Reg 13: Bit 7..5= x	5.7 kHz	3.3 mA	Temperature enabled (default). 1Mbit example
	Reg 11, Bit 0..1 = 11 Reg 13, Bit 7..5= x	7.5 kHz	3.3 mA	Temperature disabled (Reg 10: Bit 7 = 1). 1Mbit example
MCM (Master Controlled Mode: I <sup>2</sup> C triggered)	Reg 11: Bit 0..1 = 01 Reg 13: Bit 6 = x	0 Hz ... 7.5 kHz ~2.8 kHz	<1 $\mu A$ ... 3.3 mA ~1.7 mA	400 kbit example

- 1) Default low power setting also used to signal a sensor error.

I<sup>2</sup>C triggered mode typ. consumption ( $\mu C$  triggers every “trigger\_period”) estimation formula:

$$I_{DD} [mA] \approx 3.3 [mA] * 0.18 [ms] / \text{trigger\_period} [ms]$$



Interface and Timing Description

## 4 Interface and Timing Description

This chapter refers to how to set the boundary conditions in order to establish a proper interface communication.

**Table 13** Interface and timing<sup>1)</sup>

Parameter	Symbol	min	typ	max	Unit	Note/Condition
End-of-Conversion /INT pulse	$t_{INT}$	-	2.5	-	$\mu$ s	low-active (when activated)
Time window to read first value	$t_{RD1}$	-	40	-	$\mu$ s	read after rising /INT edge
Time window to read next value	$t_{RDn}$	-	43	-	$\mu$ s	consecutive reads
Internal clock accuracy	$t_{clk\_E}$	-25	-	+25	%	all above timing parameters
Allowed I <sup>2</sup> C bit clock frequency	$f_{I2C\_clk}$	-	400	1000	kHz	400kHz is I <sup>2</sup> C fast mode
Low period of SCL clock	$t_L$	0.5	-	-	$\mu$ s	1.3 $\mu$ s for 400kHz mode
High period of SCL clock	$t_H$	0.4	-	-	$\mu$ s	0.6 $\mu$ s for 400kHz mode
SDA fall to SCL fall hold time (hold time start condition to clock)	$t_{STA}$	0.4	-	-	$\mu$ s	0.6 $\mu$ s for 400kHz mode
SCL rise to SDA rise su. time (setup time clock to stop condition)	$t_{STOP}$	0.4	-	-	$\mu$ s	0.6 $\mu$ s for 400kHz mode
SDA rise to SDA fall hold time (wait time from stop to start cond.)	$t_{WAIT}$	0.4	-	-	$\mu$ s	0.6 $\mu$ s for 400kHz mode
SDA setup before SCL rising	$t_{SU}$	0.1	-	-	$\mu$ s	-
SDA hold after SCL falling	$t_{HOLD}$	0	-	-	$\mu$ s	-
Fall time SDA/SCL signal <sup>2)</sup>	$t_{FALL}$	-	0.05 <sup>3)</sup>	0.3	$\mu$ s	0.3 $\mu$ s for 400kHz mode (or may require less C load)
Rise time SDA/SCL signal <sup>2)</sup>	$t_{RISE}$	-	0.6 <sup>3)</sup>	-	$\mu$ s	R = 1.2k

1) Not subject to production test - verified by design/characterization

2) Dependent on used R-C-combination

3) For given AppCircuit; Capacitive load for each bus line = 200pF (SDA, SCL)

Interface and Timing Description

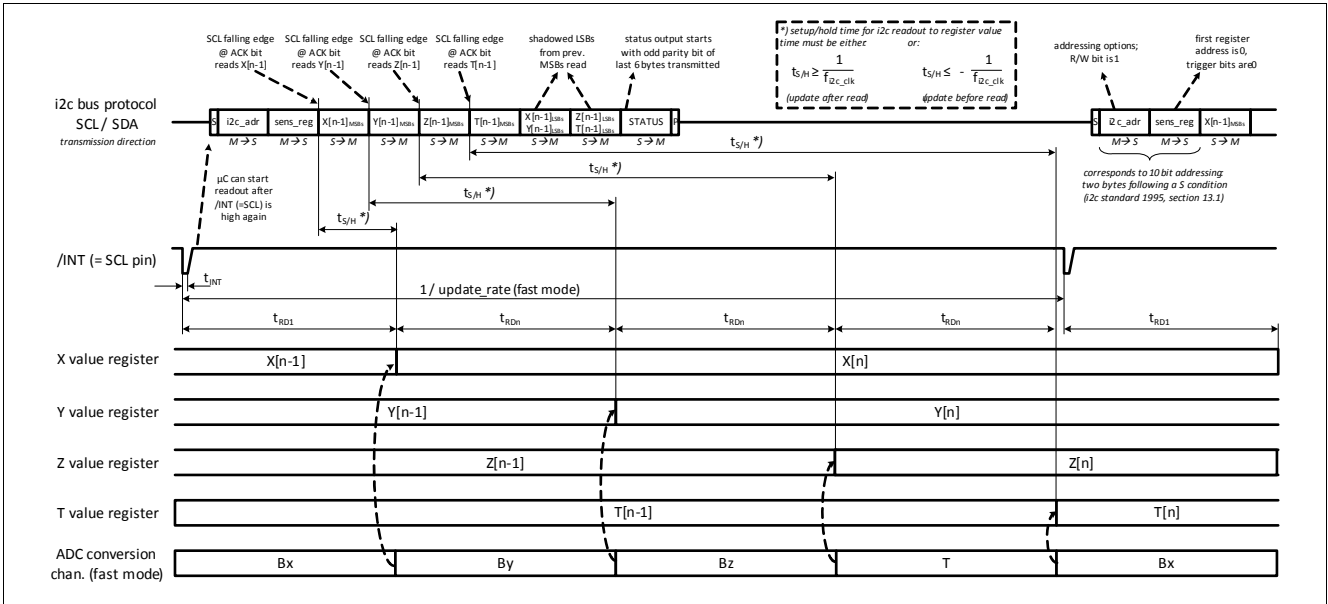


Figure 7 I<sup>2</sup>C readout frame, ADC conversion and related timing

Note: The fast mode requires a very strict I<sup>2</sup>C behavior synchronized with the sensor conversions and high bit rates; other modes are available for more relaxed timing and also for a synchronous  $\mu$ C operation of sensor conversions; in 3-channel mode, the T chan. is not converted and updated (so the cycle starts over with Bx after Bz is finished); in all other modes the conversion stops after the T chan. (or Bz chan. in 3-channel mode) until it is triggered again by an internal or external trigger source (which will start an Bx chan. conv.).

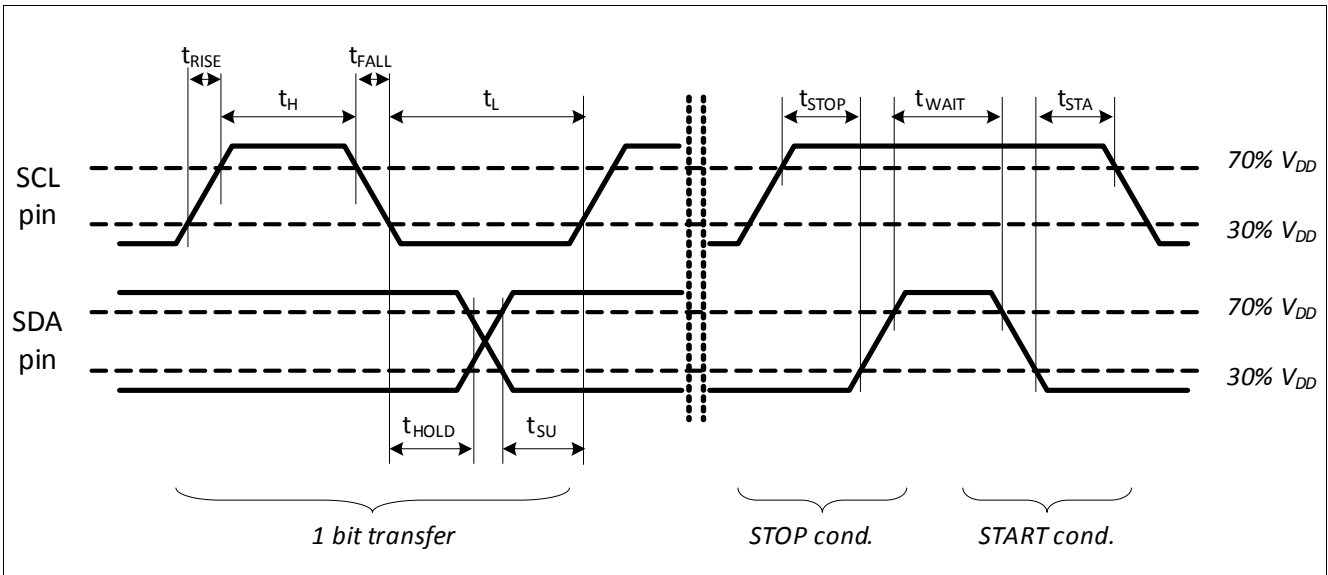


Figure 8 I<sup>2</sup>C timing specification

Package Information

## 5 Package Information

### 5.1 Package Parameters

Table 14 Package Parameters

Parameter	Symbol	Limit Values			Unit	Notes
		Min.	Typ.	Max.		
Thermal resistance Junction ambient	$R_{thJA}$	-	-	200	K/W	Junction to air <sup>1)</sup> for PG-TSOP-6-6-5
Thermal resistance Junction lead	$R_{thJL}$	-	-	100	K/W	Junction to lead for PG-TSOP-6-6-5
Moisture Sensitivity Level	MSL 1					260°C <sup>2)</sup>

1) according to Jedec JESD51-7

2) suitable for reflow soldering with soldering profiles according to JEDEC J-STD-020D.1 (March 2008)

### 5.2 Package Outlines

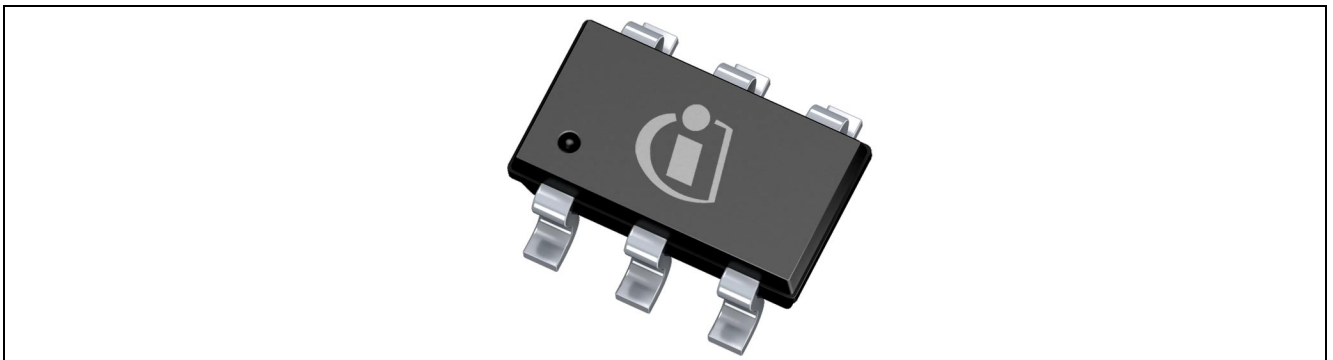


Figure 9 Image of TLE493D-A1B6 in TSOP6

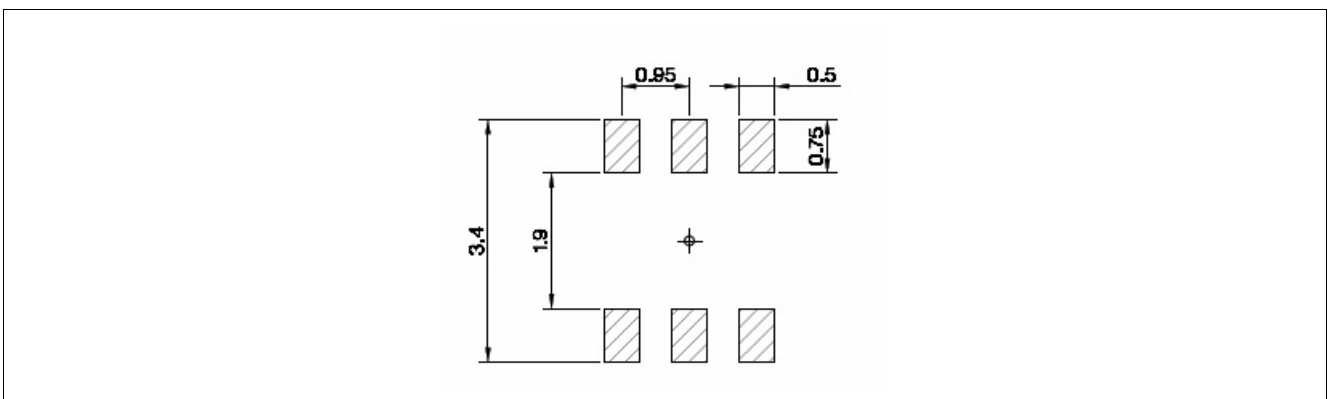


Figure 10 Footprint for PG-TSOP6-6-5 and PG-TSOP6-6-8 (all dimensions in mm)



Package Information

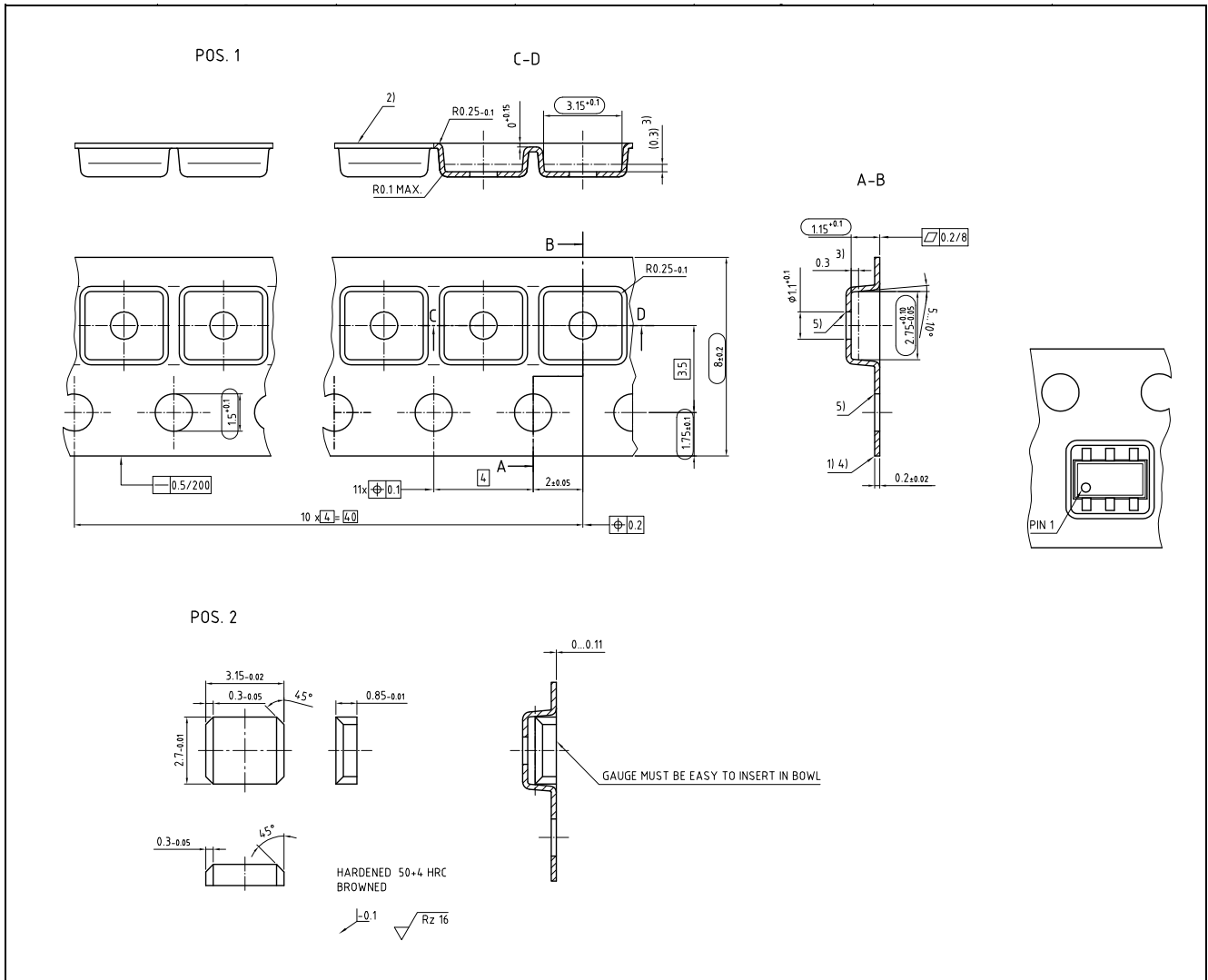


Figure 12 Packing (all dimensions in mm)

Further Information about the package can be found here:

[http://www.infineon.com/cms/packages/SMD\\_-\\_Surface\\_Mounted\\_Devices/TSOP/TSOP6.html](http://www.infineon.com/cms/packages/SMD_-_Surface_Mounted_Devices/TSOP/TSOP6.html)

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Revision History

## 6 Revision History

Revision	Date	Changes
Rev. 1.2	2019-04-09	<a href="#">Note on Page 12</a> updated.
Rev. 1.1	2017-11-07	<a href="#">Chapter 1.2</a> editorial changes. <a href="#">Figure 5</a> updated. <a href="#">Table 8</a> Offset drift updated.
Rev. 1.0	2017-02-10	Initial version

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